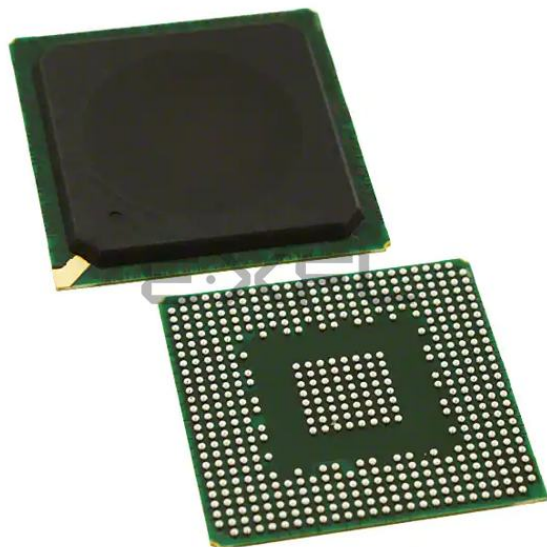




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Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	516-BBGA Exposed Pad
Supplier Device Package	516-TEPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8313cvraffb

1.2 Serial Interfaces

The following interfaces are supported in the MPC8313E: dual UART, dual I²C, and an SPI interface.

1.3 Security Engine

The security engine is optimized to handle all the algorithms associated with IPSec, IEEE Std 802.11i®, and iSCSI. The security engine contains one crypto-channel, a controller, and a set of crypto execution units (EUs). The execution units are as follows:

- Data encryption standard execution unit (DEU), supporting DES and 3DES
- Advanced encryption standard unit (AESU), supporting AES
- Message digest execution unit (MDEU), supporting MD5, SHA1, SHA-224, SHA-256, and HMAC with any algorithm
- One crypto-channel supporting multi-command descriptor chains

1.4 DDR Memory Controller

The MPC8313E DDR1/DDR2 memory controller includes the following features:

- Single 16- or 32-bit interface supporting both DDR1 and DDR2 SDRAM
- Support for up to 333 MHz
- Support for two physical banks (chip selects), each bank independently addressable
- 64-Mbit to 2-Gbit (for DDR1) and to 4-Gbit (for DDR2) devices with x8/x16/x32 data ports (no direct x4 support)
- Support for one 16-bit device or two 8-bit devices on a 16-bit bus, or one 32-bit device or two 16-bit devices on a 32-bit bus
- Support for up to 16 simultaneous open pages
- Supports auto refresh
- On-the-fly power management using CKE
- 1.8-/2.5-V SSTL2 compatible I/O

1.5 PCI Controller

The MPC8313E PCI controller includes the following features:

- PCI specification revision 2.3 compatible
- Single 32-bit data PCI interface operates at up to 66 MHz
- PCI 3.3-V compatible (not 5-V compatible)
- Support for host and agent modes
- On-chip arbitration, supporting three external masters on PCI
- Selectable hardware-enforced coherency

1.6 USB Dual-Role Controller

The MPC8313E USB controller includes the following features:

- Supports USB on-the-go mode, which includes both device and host functionality, when using an external ULPI (UTMI + low-pin interface) PHY
- Compatible with *Universal Serial Bus Specification, Rev. 2.0*
- Supports operation as a stand-alone USB device
 - Supports one upstream facing port
 - Supports three programmable USB endpoints
- Supports operation as a stand-alone USB host controller
 - Supports USB root hub with one downstream-facing port
 - Enhanced host controller interface (EHCI) compatible
- Supports high-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operation. Low-speed operation is supported only in host mode.
- Supports UTMI + low pin interface (ULPI) or on-chip USB 2.0 full-speed/high-speed PHY

1.7 Dual Enhanced Three-Speed Ethernet Controllers (eTSECs)

The MPC8313E eTSECs include the following features:

- Two RGMII/SGMII/MII/RMII/RTBI interfaces
- Two controllers designed to comply with IEEE Std 802.3®, 802.3u®, 802.3x®, 802.3z®, 802.3au®, and 802.3ab®
- Support for Wake-on-Magic Packet™, a method to bring the device from standby to full operating mode
- MII management interface for external PHY control and status
- Three-speed support (10/100/1000 Mbps)
- On-chip high-speed serial interface to external SGMII PHY interface
- Support for IEEE Std 1588™
- Support for two full-duplex FIFO interface modes
- Multiple PHY interface configuration
- TCP/IP acceleration and QoS features available
- IP v4 and IP v6 header recognition on receive
- IP v4 header checksum verification and generation
- TCP and UDP checksum verification and generation
- Per-packet configurable acceleration
- Recognition of VLAN, stacked (queue in queue) VLAN, IEEE Std 802.2®, PPPoE session, MPLS stacks, and ESP/AH IP-security headers
- Transmission from up to eight physical queues.
- Reception to up to eight physical queues

- Full and half-duplex Ethernet support (1000 Mbps supports only full-duplex):
 - IEEE 802.3 full-duplex flow control (automatic PAUSE frame generation or software-programmed PAUSE frame generation and recognition)
 - Programmable maximum frame length supports jumbo frames (up to 9.6 Kbytes) and IEEE 802.1 virtual local area network (VLAN) tags and priority
 - VLAN insertion and deletion
 - Per-frame VLAN control word or default VLAN for each eTSEC
 - Extracted VLAN control word passed to software separately
 - Retransmission following a collision
 - CRC generation and verification of inbound/outbound packets
 - Programmable Ethernet preamble insertion and extraction of up to 7 bytes
- MAC address recognition:
 - Exact match on primary and virtual 48-bit unicast addresses
 - VRRP and HSRP support for seamless router fail-over
 - Up to 16 exact-match MAC addresses supported
 - Broadcast address (accept/reject)
 - Hash table match on up to 512 multicast addresses
 - Promiscuous mode
- Buffer descriptors backward compatible with MPC8260 and MPC860T 10/100 Ethernet programming models
- RMON statistics support
- 10-Kbyte internal transmit and 2-Kbyte receive FIFOs
- MII management interface for control and status

1.8 Programmable Interrupt Controller (PIC)

The programmable interrupt controller (PIC) implements the necessary functions to provide a flexible solution for general-purpose interrupt control. The PIC programming model supports 5 external and 34 internal discrete interrupt sources. Interrupts can also be redirected to an external interrupt controller.

1.9 Power Management Controller (PMC)

The MPC8313E power management controller includes the following features:

- Provides power management when the device is used in both host and agent modes
- Supports PCI power management 1.2 D0, D1, D2, D3hot, and D3cold states
- On-chip split power supply controlled through external power switch for minimum standby power
- Support for PME generation in PCI agent mode, PME detection in PCI host mode
- Supports wake-up from Ethernet (Magic Packet), USB, GPIO, and PCI (PME input as host)

1.10 Serial Peripheral Interface (SPI)

The serial peripheral interface (SPI) allows the MPC8313E to exchange data between other PowerQUICC family chips, Ethernet PHYs for configuration, and peripheral devices such as EEPROMs, real-time clocks, A/D converters, and ISDN devices.

The SPI is a full-duplex, synchronous, character-oriented channel that supports a four-wire interface (receive, transmit, clock, and slave select). The SPI block consists of transmitter and receiver sections, an independent baud-rate generator, and a control unit.

1.11 DMA Controller, Dual I²C, DUART, Local Bus Controller, and Timers

The MPC8313E provides an integrated four-channel DMA controller with the following features:

- Allows chaining (both extended and direct) through local memory-mapped chain descriptors (accessible by local masters)
- Supports misaligned transfers

There are two I²C controllers. These synchronous, multi-master buses can be connected to additional devices for expansion and system development.

The DUART supports full-duplex operation and is compatible with the PC16450 and PC16550 programming models. The 16-byte FIFOs are supported for both the transmitter and the receiver.

The MPC8313E local bus controller (LBC) port allows connections with a wide variety of external DSPs and ASICs. Three separate state machines share the same external pins and can be programmed separately to access different types of devices. The general-purpose chip select machine (GPCM) controls accesses to asynchronous devices using a simple handshake protocol. The three user programmable machines (UPMs) can be programmed to interface to synchronous devices or custom ASIC interfaces. Each chip select can be configured so that the associated chip interface can be controlled by the GPCM or UPM controller. The FCM provides a glueless interface to parallel-bus NAND Flash E2PROM devices. The FCM contains three basic configuration register groups—BR n , OR n , and FMR. Both may exist in the same system. The local bus can operate at up to 66 MHz.

The MPC8313E system timers include the following features: periodic interrupt timer, real time clock, software watchdog timer, and two general-purpose timer blocks.

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8313E. The MPC8313E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value ¹	Unit	Current Requirement
Core supply voltage	V_{DD}	1.0 V $\pm$ 50 mV	V	469 mA
Internal core logic constant power	V_{DDC}	1.0 V $\pm$ 50 mV	V	377 mA
SerDes internal digital power	$XCOREV_{DD}$	1.0	V	170 mA
SerDes internal digital ground	$XCOREV_{SS}$	0.0	V	—
SerDes I/O digital power	$XPADV_{DD}$	1.0	V	10 mA
SerDes I/O digital ground	$XPADV_{SS}$	0.0	V	—
SerDes analog power for PLL	$SDAV_{DD}$	1.0 V $\pm$ 50 mV	V	10 mA
SerDes analog ground for PLL	$SDAV_{SS}$	0.0	V	—
Dedicated 3.3 V analog power for USB PLL	USB_PLL_PWR3	3.3 V $\pm$ 300 mV	V	2–3 mA
Dedicated 1.0 V analog power for USB PLL	USB_PLL_PWR1	1.0 V $\pm$ 50 mV	V	2–3 mA
Dedicated analog ground for USB PLL	USB_PLL_GND	0.0	V	—
Dedicated USB power for USB bias circuit	USB_VDDA_BIAS	3.3 V $\pm$ 300 mV	V	4–5 mA
Dedicated USB ground for USB bias circuit	USB_VSSA_BIAS	0.0	V	—
Dedicated power for USB transceiver	USB_VDDA	3.3 V $\pm$ 300 mV	V	75 mA
Dedicated ground for USB transceiver	USB_VSSA	0.0	V	—
Analog power for e300 core APLL	AV_{DD1} ⁶	1.0 V $\pm$ 50 mV	V	2–3 mA
Analog power for system APLL	AV_{DD2} ⁶	1.0 V $\pm$ 50 mV	V	2–3 mA
DDR1 DRAM I/O voltage (333 MHz, 32-bit operation)	GV_{DD}	2.5 V $\pm$ 125 mV	V	131 mA
DDR2 DRAM I/O voltage (333 MHz, 32-bit operation)	GV_{DD}	1.8 V $\pm$ 80 mV	V	140 mA
Differential reference voltage for DDR controller	MV_{REF}	1/2 DDR supply ($0.49 \times GV_{DD}$ to $0.51 \times GV_{DD}$)	V	—
Standard I/O voltage	NV_{DD}	3.3 V $\pm$ 300 mV ²	V	74 mA
eTSEC2 I/O supply	LV_{DDA}	2.5 V $\pm$ 125 mV/ 3.3 V $\pm$ 300 mV	V	22 mA
eTSEC1/USB DR I/O supply	LV_{DDB}	2.5 V $\pm$ 125 mV/ 3.3 V $\pm$ 300 mV	V	44 mA
Supply for eLBC I/Os	LV_{DD}	3.3 V $\pm$ 300 mV	V	16 mA
Analog and digital ground	V_{SS}	0.0	V	—
Junction temperature range	T_A/T_J ³	0 to 105	°C	

4.2 AC Electrical Characteristics

The primary clock source for the MPC8313E can be one of two inputs, SYS_CLK_IN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. This table provides the system clock input (SYS_CLK_IN/PCI_CLK) AC timing specifications for the MPC8313E.

Table 8. SYS_CLK_IN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Note
SYS_CLK_IN/PCI_CLK frequency	$f_{\text{SYS_CLK_IN}}$	24	—	66.67	MHz	1
SYS_CLK_IN/PCI_CLK cycle time	$t_{\text{SYS_CLK_IN}}$	15	—	—	ns	—
SYS_CLK_IN rise and fall time	$t_{\text{KH}}, t_{\text{KL}}$	0.6	0.8	4	ns	2
PCI_CLK rise and fall time	$t_{\text{PCH}}, t_{\text{PCL}}$	0.6	0.8	1.2	ns	2
SYS_CLK_IN/PCI_CLK duty cycle	$t_{\text{KHK}}/t_{\text{SYS_CLK_IN}}$	40	—	60	%	3
SYS_CLK_IN/PCI_CLK jitter	—	—	—	±150	ps	4, 5

Notes:

1. **Caution:** The system, core, security block must not exceed their respective maximum or minimum operating frequencies.
2. Rise and fall times for SYS_CLK_IN/PCI_CLK are measured at 0.4 and 2.4 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The SYS_CLK_IN/PCI_CLK driver's closed loop jitter bandwidth should be <500 kHz at -20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYS_CLK_IN drivers with the specified jitter.

5 RESET Initialization

This section describes the DC and AC electrical specifications for the reset initialization timing and electrical requirements of the MPC8313E.

5.1 RESET DC Electrical Characteristics

This table provides the DC electrical characteristics for the RESET pins.

Table 9. RESET Pins DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.1	$NV_{\text{DD}} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \leq V_{\text{IN}} \leq NV_{\text{DD}}$	—	±5	μA
Output high voltage	V_{OH}	$I_{\text{OH}} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{\text{OL}} = 8.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{\text{OL}} = 3.2 \text{ mA}$	—	0.4	V

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications for Rev. 1.0 Silicon

Parameter	Symbol ¹	Min	Max	Unit	Note
MCK[n] cycle time, MCK[n]/MCK[n] crossing	t_{MCK}	6	10	ns	2
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz	t_{DDKHAS}	2.1 2.5	— —	ns	3
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz	t_{DDKHAX}	2.4 3.15	— —	ns	3
MCS[n] output setup with respect to MCK 333 MHz 266 MHz	t_{DDKHCS}	2.4 3.15	— —	ns	3
MCS[n] output hold with respect to MCK 333 MHz 266 MHz	$t_{DDKH CX}$	2.4 3.15	— —	ns	3
MCK to MDQS Skew	t_{DDKMHM}	−0.6	0.6	ns	4
MDQ//MDM output setup with respect to MDQS 333 MHz 266 MHz	t_{DDKHDS} , t_{DDKLDS}	800 900	— —	ps	5
MDQ//MDM output hold with respect to MDQS 333 MHz 266 MHz	t_{DDKHDX} , $t_{DDKL DX}$	900 1100	— —	ps	5
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6
MDQS epilogue end	t_{DDKHME}	−0.6	0.6	ns	6

Notes:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, $t_{DDKL DX}$ symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
- All MCK/MCK referenced measurements are made from the crossing of the two signals ± 0.1 V.
- ADDR/CMD includes all DDR SDRAM output signals except MCK/MCK, MCS, and MDQ//MDM/MDQS.
- Note that t_{DDKMHM} follows the symbol conventions described in note 1. For example, t_{DDKMHM} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKMHM} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8313E PowerQUICC II Pro Integrated Processor Family Reference Manual*, for a description and understanding of the timing modifications enabled by use of these bits.
- Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
- All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Table 21. DDR and DDR2 SDRAM Output AC Timing Specifications for Silicon Rev 2.x or Later

Parameter	Symbol ¹	Min	Max	Unit	Note
MCK[n] cycle time, MCK[n]/MCK[n] crossing	t_{MCK}	6	10	ns	2
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz	t_{DDKHAS}	2.1 2.5	— —	ns	3
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz	t_{DDKHAX}	2.0 2.7	— —	ns	3
MCS[n] output setup with respect to MCK 333 MHz 266 MHz	t_{DDKHCS}	2.1 3.15	— —	ns	3
MCS[n] output hold with respect to MCK 333 MHz 266 MHz	$t_{DDKHCSX}$	2.0 2.7	— —	ns	3
MCK to MDQS Skew	t_{DDKMHM}	−0.6	0.6	ns	4
MDQ//MDM output setup with respect to MDQS 333 MHz 266 MHz	t_{DDKHDS} , t_{DDKLDS}	800 900	— —	ps	5
MDQ//MDM output hold with respect to MDQS 333 MHz 266 MHz	t_{DDKHDX} , t_{DDKLDX}	750 1000	— —	ps	5
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6
MDQS epilogue end	t_{DDKHME}	−0.6	0.6	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/MCK referenced measurements are made from the crossing of the two signals ± 0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/MCK, MCS, and MDQ//MDM/MDQS.
4. Note that t_{DDKMHM} follows the symbol conventions described in note 1. For example, t_{DDKMHM} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKMHM} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8313E PowerQUICC II Pro Integrated Processor Family Reference Manual*, for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Table 25. RGMII/RTBI DC Electrical Characteristics (continued)

Parameters	Symbol	Conditions		Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -1.0 \text{ mA}$	LV_{DDA} or $LV_{DDB} = \text{Min}$	2.00	$LV_{DDA} + 0.3$ or $LV_{DDB} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 1.0 \text{ mA}$	LV_{DDA} or $LV_{DDB} = \text{Min}$	$V_{SS} - 0.3$	0.40	V
Input high voltage	V_{IH}	—	LV_{DDA} or $LV_{DDB} = \text{Min}$	1.7	$LV_{DDA} + 0.3$ or $LV_{DDB} + 0.3$	V
Input low voltage	V_{IL}	—	LV_{DDA} or $LV_{DDB} = \text{Min}$	-0.3	0.70	V
Input high current	I_{IH}	$V_{IN}^1 = LV_{DDA}$ or LV_{DDB}		—	10	μA
Input low current	I_{IL}	$V_{IN}^1 = V_{SS}$		-15	—	μA

Note:

- Note that the symbol V_{IN} , in this case, represents the LV_{IN} symbol referenced in [Table 1](#) and [Table 2](#).

8.2 MII, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for MII, RMII, RGMII, and RTBI are presented in this section.

8.2.1 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.1.1 MII Transmit AC Timing Specifications

This table provides the MII transmit AC timing specifications.

Table 26. MII Transmit AC Timing Specifications

At recommended operating conditions with $LV_{DDA}/LV_{DDB}/NV_{DD}$ of $3.3 \text{ V} \pm 0.3 \text{ V}$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise $V_{IL}(\text{min})$ to $V_{IH}(\text{max})$	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall $V_{IH}(\text{max})$ to $V_{IL}(\text{min})$	t_{MTXF}	1.0	—	4.0	ns

Note:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure shows the MII receive AC timing diagram.

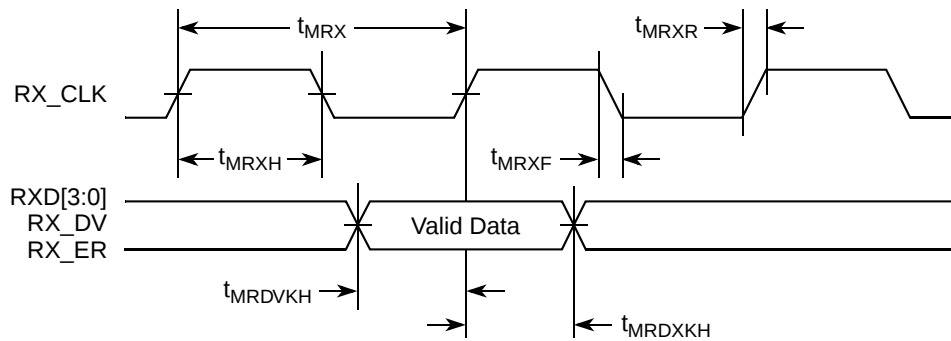


Figure 10. MII Receive AC Timing Diagram RMII AC Timing Specifications

8.2.1.3 RMII Transmit AC Timing Specifications

This table provides the RMII transmit AC timing specifications.

Table 28. RMII Transmit AC Timing Specifications

At recommended operating conditions with V_{DD} of $3.3\text{ V} \pm 0.3\text{ V}$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
REF_CLK clock	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
REF_CLK to RMII data TXD[1:0], TX_EN delay	$t_{RMTKHDX}$	2	—	10	ns
REF_CLK data clock rise $V_{IL}(\text{min})$ to $V_{IH}(\text{max})$	t_{RMXR}	1.0	—	4.0	ns
REF_CLK data clock fall $V_{IH}(\text{max})$ to $V_{IL}(\text{min})$	t_{RMXF}	1.0	—	4.0	ns

Note:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first three letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, $t_{RMTKHDX}$ symbolizes RMII transmit timing (RMT) for the time t_{RMX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII(RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure shows the RMII transmit AC timing diagram.

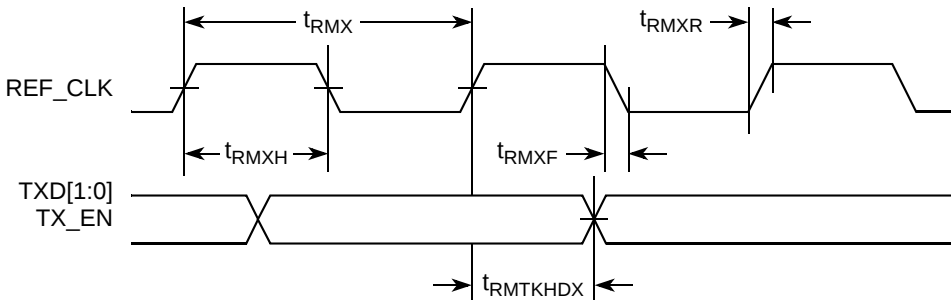


Figure 11. RMII Transmit AC Timing Diagram

Table 36. eTSEC IEEE 1588 AC Timing Specifications (continued)

At recommended operating conditions with L/TV_{DD} of 3.3 V $\pm$ 5%.

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Note
TSEC_1588_CLK peak-to-peak jitter	$t_{T1588CLKINJ}$	—	—	250	ps	
Rise time eTSEC_1588_CLK (20%–80%)	$t_{T1588CLKINR}$	1.0	—	2.0	ns	
Fall time eTSEC_1588_CLK (80%–20%)	$t_{T1588CLKINF}$	1.0	—	2.0	ns	
TSEC_1588_CLK_OUT clock period	$t_{T1588CLKOUT}$	$2 \times t_{T1588CLK}$	—	—	ns	
TSEC_1588_CLK_OUT duty cycle	$t_{T1588CLKOTH} / t_{T1588CLKOUT}$	30	50	70	%	
TSEC_1588_PULSE_OUT	$t_{T1588OV}$	0.5	—	3.0	ns	
TSEC_1588_TRIG_IN pulse width	$t_{T1588TRIGH}$	$2 \times t_{T1588CLK_MAX}$	—	—	ns	2

Notes:

1. T_{RX_CLK} is the max clock period of eTSEC receiving clock selected by TMR_CTRL[CKSEL]. See the *MPC8313E PowerQUICC II Pro Integrated Processor Family Reference Manual*, for a description of TMR_CTRL registers.
2. It need to be at least two times of clock period of clock selected by TMR_CTRL[CKSEL]. See the *MPC8313E PowerQUICC II Pro Integrated Processor Family Reference Manual*, for a description of TMR_CTRL registers.
3. The maximum value of $t_{T1588CLK}$ is not only defined by the value of T_{RX_CLK} , but also defined by the recovered clock. For example, for 10/100/1000 Mbps modes, the maximum value of $t_{T1588CLK}$ is 3600, 280, and 56 ns, respectively.

8.5 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for MII, RMII, RGMII, SGMII, and RTBI are specified in [Section 8.1, “Enhanced Three-Speed Ethernet Controller \(eTSEC\) \(10/100/1000 Mbps\)—MII/RMII/RGMII/SGMII/RTBI Electrical Characteristics.”](#)

8.5.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. [Table 37](#) provide the DC electrical characteristics for MDIO and MDC.

Table 37. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	NV_{DD}	—		2.97	3.63	V
Output high voltage	V_{OH}	$I_{OH} = -1.0$ mA	$NV_{DD} = \text{Min}$	2.10	$NV_{DD} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 1.0$ mA	$NV_{DD} = \text{Min}$	V_{SS}	0.50	V
Input high voltage	V_{IH}	—		2.0	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input high current	I_{IH}	$NV_{DD} = \text{Max}$	$V_{IN}^1 = 2.1$ V	—	40	μA
Input low current	I_{IL}	$NV_{DD} = \text{Max}$	$V_{IN} = 0.5$ V	–600	—	μA

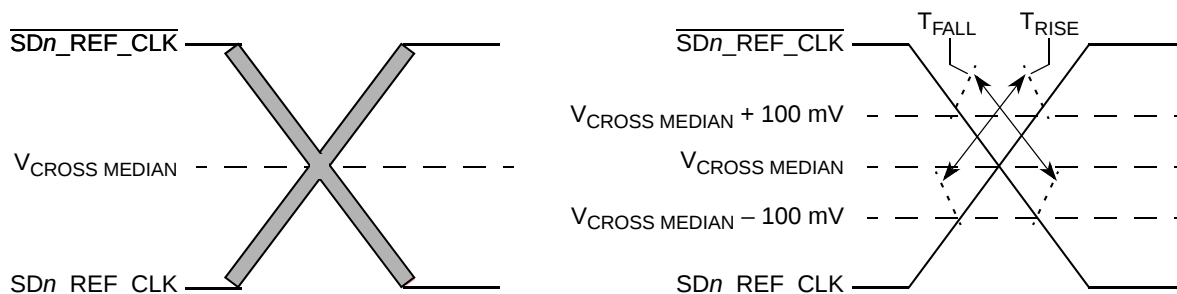


Figure 32. Single-Ended Measurement Points for Rise and Fall Time Matching

The other detailed AC requirements of the SerDes reference clocks is defined by each interface protocol based on application usage. Refer to the following section for detailed information:

- [Section 8.3.2, “AC Requirements for SGMII SD_REF_CLK and SD_REF_CLK”](#)

9.2.4.1 Spread Spectrum Clock

SD_REF_CLK/ $\overline{\text{SD_REF_CLK}}$ are not intended to be used with, and should not be clocked by, a spread spectrum clock source.

9.3 SerDes Transmitter and Receiver Reference Circuits

This figure shows the reference circuits for the SerDes data lane’s transmitter and receiver.

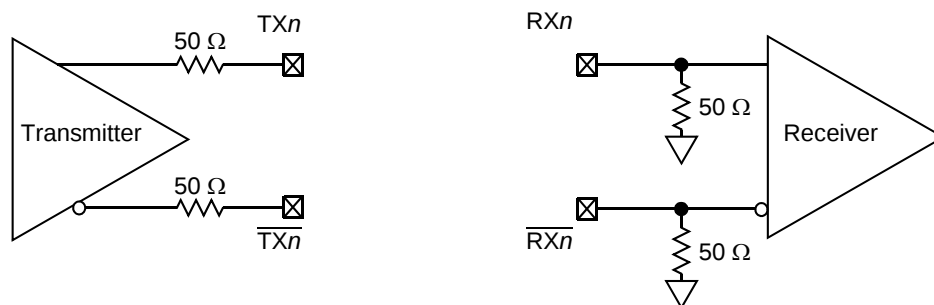


Figure 33. SerDes Transmitter and Receiver Reference Circuits

The SerDes data lane’s DC and AC specifications are defined in the interface protocol section listed below (SGMII) based on the application usage:

- [Section 8.3, “SGMII Interface Electrical Characteristics”](#)

Please note that a external AC-coupling capacitor is required for the above serial transmission protocol with the capacitor value defined in the specifications of the protocol section.

Figure 37 through Figure 40 show the local bus signals.

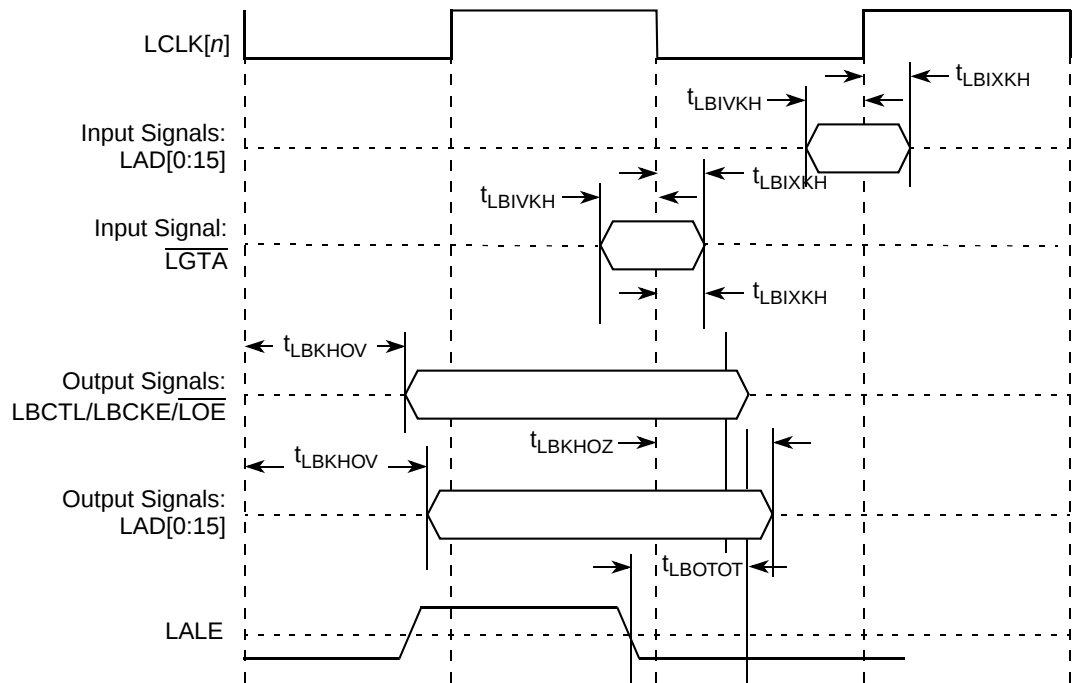


Figure 37. Local Bus Signals, Non-Special Signals Only

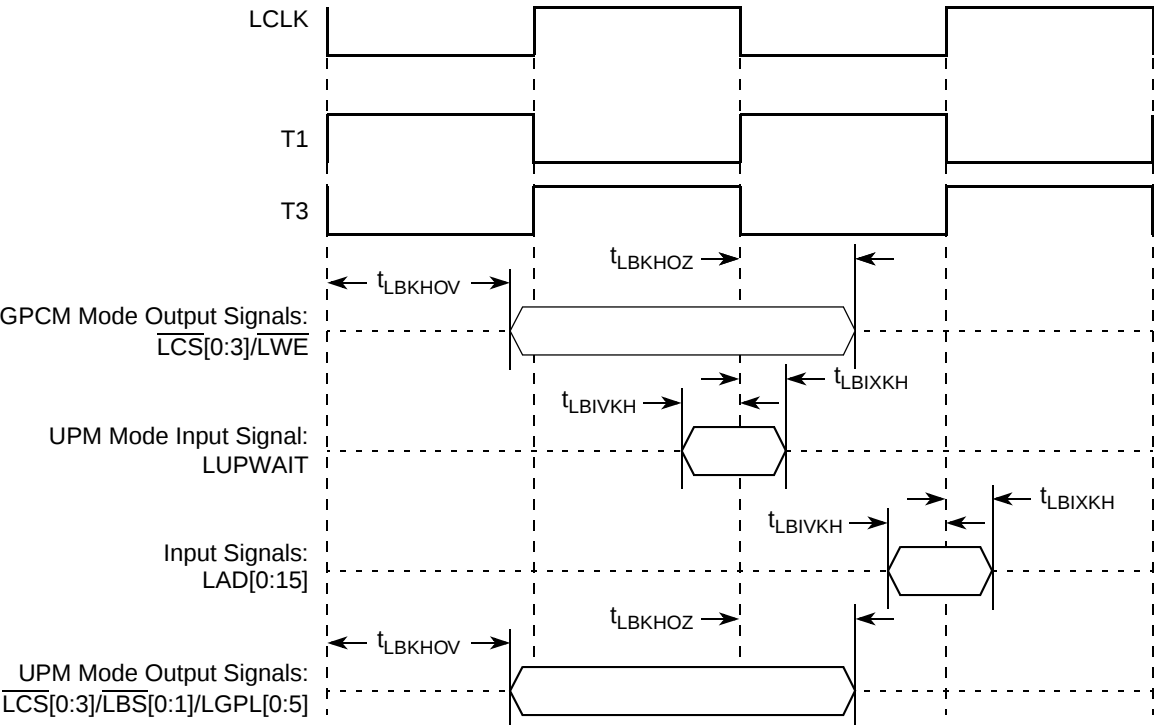


Figure 38. Local Bus Signals, GPCM/UPM Signals for $LCRR[CLKDIV] = 2$

15.2 Timers AC Timing Specifications

This table provides the Timers input and output AC timing specifications.

Table 54. Timers Input AC Timing Specifications¹

Characteristic	Symbol ²	Min	Unit
Timers inputs—minimum pulse width	t_{TIWID}	20	ns

Notes:

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of SYS_CLK_IN. Timings are measured at the pin.
2. Timers inputs and outputs are asynchronous to any visible clock. Timers outputs should be synchronized before use by any external synchronous logic. Timers inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation

This figure provides the AC test load for the Timers.

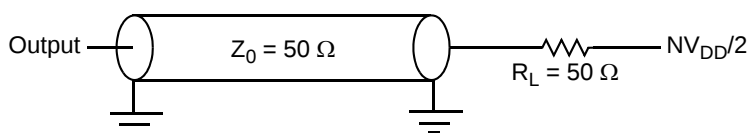


Figure 51. Timers AC Test Load

16 GPIO

This section describes the DC and AC electrical specifications for the GPIO.

16.1 GPIO DC Electrical Characteristics

This table provides the DC electrical characteristics for the GPIO when the GPIO pins are operating from a 3.3-V supply.

Table 55. GPIO (When Operating at 3.3 V) DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V
Input high voltage	V_{IH}	—	2.0	$NV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq NV_{DD}$	—	± 5	μA

Note:

1. This specification only applies to GPIO pins that are operating from a 3.3-V supply. See [Table 62](#) for the power supply listed for the individual GPIO signal.

Table 60. SPI DC Electrical Characteristics (continued)

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.1	$NV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	−0.3	0.8	V
Input current	I_{IN}	$0\text{ V} \leq V_{IN} \leq NV_{DD}$	—	±5	μA

18.2 SPI AC Timing Specifications

This table and provide the SPI input and output AC timing specifications.

Table 61. SPI AC Timing Specifications¹

Characteristic	Symbol ²	Min	Max	Unit
SPI outputs—master mode (internal clock) delay	$t_{NIKH OV}$	0.5	6	ns
SPI outputs—slave mode (external clock) delay	$t_{NEKH OV}$	2	8	ns
SPI inputs—master mode (internal clock) input setup time	t_{NIIVKH}	6	—	ns
SPI inputs—master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Note:

- Output specifications are measured from the 50% level of the rising edge of SYS_CLK_IN to the 50% level of the signal. Timings are measured at the pin.
- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, $t_{NIKH OV}$ symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).

This figure provides the AC test load for the SPI.

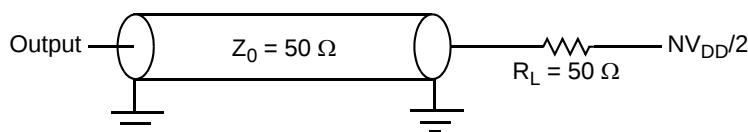


Figure 53. SPI AC Test Load

Figure 54 and Figure 55 represent the AC timing from Table 61. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Table 62. MPC8313E TEPBGAI Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
TSEC1_TXD1/TSEC_1588_PP2	AD6	O	LV _{DDB}	—
TSEC1_TXD0/USBDR_STP/TSEC_1588_PP3	AD5	O	LV _{DDB}	—
TSEC1_TX_EN/TSEC_1588_ALARM1	AB7	O	LV _{DDB}	—
TSEC1_TX_ER/TSEC_1588_ALARM2	AB8	O	LV _{DDB}	—
TSEC1_GTX_CLK125	AE1	I	LV _{DDB}	—
TSEC1_MDC/LB_POR_CFG_BOOT_ECC_DIS	AF6	O	NV _{DD}	9, 11
TSEC1_MDIO	AB9	I/O	NV _{DD}	—
ETSEC2				
TSEC2_COL/GTM1_TIN4/GTM2_TIN3/GPIO15	AB4	I/O	LV _{DDA}	—
TSEC2_CRS/GTM1_TGATE4/GTM2_TGATE3/GPIO16	AB3	I/O	LV _{DDA}	—
TSEC2_GTX_CLK/GTM1_TOUT4/GTM2_TOUT3/GPIO17	AC1	I/O	LV _{DDA}	12
TSEC2_RX_CLK/GTM1_TIN2/GTM2_TIN1/GPIO18	AC2	I/O	LV _{DDA}	—
TSEC2_RX_DV/GTM1_TGATE2/GTM2_TGATE1/GPIO19	AA3	I/O	LV _{DDA}	—
TSEC2_RXD3/GPIO20	Y5	I/O	LV _{DDA}	—
TSEC2_RXD2/GPIO21	AA4	I/O	LV _{DDA}	—
TSEC2_RXD1/GPIO22	AB2	I/O	LV _{DDA}	—
TSEC2_RXD0/GPIO23	AA5	I/O	LV _{DDA}	—
TSEC2_RX_ER/GTM1_TOUT2/GTM2_TOUT1/GPIO24	AA2	I/O	LV _{DDA}	—
TSEC2_TX_CLK/GPIO25	AB1	I/O	LV _{DDA}	—
TSEC2_TXD3/CFG_RESET_SOURCE0	W3	I/O	LV _{DDA}	—
TSEC2_TXD2/CFG_RESET_SOURCE1	Y1	I/O	LV _{DDA}	—
TSEC2_TXD1/CFG_RESET_SOURCE2	W5	I/O	LV _{DDA}	—
TSEC2_TXD0/CFG_RESET_SOURCE3	Y3	I/O	LV _{DDA}	—
TSEC2_TX_EN/GPIO26	AA1	I/O	LV _{DDA}	—
TSEC2_TX_ER/GPIO27	W1	I/O	LV _{DDA}	—
SGMII PHY				
TXA	U3	O		—
$\overline{\text{TXA}}$	V3	O		—
RXA	U1	I		—
$\overline{\text{RXA}}$	V1	I		—
TXB	P4	O		—
$\overline{\text{TXB}}$	N4	O		—

Table 62. MPC8313E TEPBGAI Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
V _{SS}	B1,B2,B8,B9,B16,B17,C1,C2,C3,C4,C5,C24,C25,C26,D3,D4,D12,D13,D20,D21,F8,F11,F13,F16,F17,F21,G2,G25,H2,H6,H21,H25,L4,L6,L11,L12,L13,L14,L15,L16,L21,L23,M4,M11,M12,M13,M14,M15,M16,M23,N6,N11,N12,N13,N14,N15,N16,N21,N23,P11,P12,P13,P14,P15,P16,P23,P25,R11,R12,R13,R14,R15,R16,R25,T6,T11,T12,T13,T14,T15,T16,T21,T25,U5,U6,U21,W4,W23,Y4,Y23,AA8,AA11,AA13,AA16,AA17,AA21,AC4,AC5,AC12,AC13,AC20,AC21,AD1,AE2,AE8,AE9,AE16,AE17,AF2	—	—	—
XCOREV _{DD}	T1,U2,V2	Core power for SerDes transceivers (1.0 V)	—	—
XCOREV _{SS}	P2,R2,T3	—	—	—
XPADV _{DD}	P5,U4	Pad power for SerDes transceivers (1.0 V)	—	—
XPADV _{SS}	P3,V4	—	—	—

Notes:

1. This pin is an open drain signal. A weak pull-up resistor (1 k Ω) should be placed on this pin to NV_{DD}.
2. This pin is an open drain signal. A weak pull-up resistor (2–10 k Ω) should be placed on this pin to NV_{DD}.
3. This output is actively driven during reset rather than being three-stated during reset.
4. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
5. This pin should have a weak pull up if the chip is in PCI host mode. Follow PCI specifications recommendation.
6. This pin must always be tied to V_{SS}.
7. Internal thermally sensitive resistor, resistor value varies linearly with temperature. Useful for determining the junction temperature.
8. 1588 signals are available on these pins only in MPC8313 Rev 2.x or later.
9. LB_POR_CFG_BOOT_ECC_DIS is available only in MPC8313 Rev 2.x or later.
10. This pin has an internal pull-up.
11. This pin has an internal pull-down.
12. In MII mode, GTX_CLK should be pulled down by 300 Ω to V_{SS}.

20.2 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). This table shows the encodings for RCWL[COREPLL]. COREPLL values that are not listed in this table should be considered as reserved.

NOTE

Core VCO frequency = core frequency × VCO divider. The VCO divider, which is determined by RCWLR[COREPLL], must be set properly so that the core VCO frequency is in the range of 400–800 MHz.

Table 67. e300 Core PLL Configuration

RCWL[COREPLL]			<i>core_clk</i> : <i>csb_clk</i> Ratio ¹	VCO Divider (VCOD) ³
0–1	2–5	6		
<i>nn</i>	0000	0	PLL bypassed (PLL off, <i>csb_clk</i> clocks core directly)	PLL bypassed (PLL off, <i>csb_clk</i> clocks core directly)
11	<i>nnnn</i>	n	n/a	n/a
00	0001	0	1:1	2
01	0001	0	1:1	4
10	0001	0	1:1	8
00	0001	1	1.5:1	2
01	0001	1	1.5:1	4
10	0001	1	1.5:1	8
00	0010	0	2:1	2
01	0010	0	2:1	4
10	0010	0	2:1	8
00	0010	1	2.5:1	2
01	0010	1	2.5:1	4
10	0010	1	2.5:1	8
00	0011	0	3:1	2
01	0011	0	3:1	4
10	0011	0	3:1	8

Note:

1. For *core_clk*:*csb_clk* ratios of 2.5:1 and 3:1, the *core_clk* must not exceed its maximum operating frequency of 333 MHz.
2. Core VCO frequency = core frequency × VCO divider. Note that VCO divider has to be set properly so that the core VCO frequency is in the range of 400–800 MHz.

21.3 Heat Sink Attachment

When attaching heat sinks to these devices, an interface material is required. The best method is to use thermal grease and a spring clip. The spring clip should connect to the printed-circuit board, either to the board itself, to hooks soldered to the board, or to a plastic stiffener. Avoid attachment forces which would lift the edge of the package or peel the package from the board. Such peeling forces reduce the solder joint lifetime of the package. Recommended maximum force on the top of the package is 10 lb (4.5 kg) force. If an adhesive attachment is planned, the adhesive should be intended for attachment to painted or plastic surfaces and its performance verified under the application requirements.

21.3.1 Experimental Determination of the Junction Temperature with a Heat Sink

When heat sink is used, the junction temperature is determined from a thermocouple inserted at the interface between the case of the package and the interface material. A clearance slot or hole is normally required in the heat sink. Minimizing the size of the clearance is important to minimize the change in thermal performance caused by removing part of the thermal interface to the heat sink. Because of the experimental difficulties with this technique, many engineers measure the heat sink temperature and then back calculate the case temperature using a separate measurement of the thermal resistance of the interface. From this case temperature, the junction temperature is determined from the junction to case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

T_J = junction temperature (°C)

T_C = case temperature of the package

$R_{\theta JC}$ = junction-to-case thermal resistance

P_D = power dissipation

22 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8313E SYS_CLK_IN

22.1 System Clocking

The MPC8313E includes three PLLs.

1. The platform PLL (AV_{DD2}) generates the platform clock from the externally supplied SYS_CLK_IN input in PCI host mode or SYS_CLK_IN/PCI_SYNC_IN in PCI agent mode. The frequency ratio between the platform and SYS_CLK_IN is selected using the platform PLL ratio configuration bits as described in [Section 20.1, “System PLL Configuration.”](#)
2. The e300 core PLL (AV_{DD1}) generates the core clock as a slave to the platform clock. The frequency ratio between the e300 core clock and the platform clock is selected using the e300 PLL ratio configuration bits as described in [Section 20.2, “Core PLL Configuration.”](#)
3. There is a PLL for the SerDes block.

- Third, between the device and any SerDes voltage regulator there should be a 10- μ F, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100- μ F, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

22.5 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to NV_{DD} , GV_{DD} , LV_{DD} , LV_{DDA} , or LV_{DDB} as required. Unused active high inputs should be connected to V_{SS} . All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD} , NV_{DD} , GV_{DD} , LV_{DD} , LV_{DDA} , LV_{DDB} , and V_{SS} pins of the device.

22.6 Output Buffer DC Impedance

The MPC8313E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I²C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to NV_{DD} or V_{SS} . Then, the value of each resistor is varied until the pad voltage is $NV_{DD}/2$ (see Figure 60). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open), and R_P is trimmed until the voltage at the pad equals $NV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

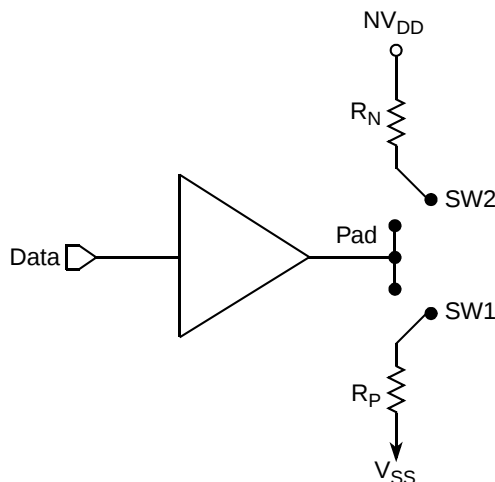


Figure 60. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term} . The measured voltage is $V_2 = (1/(1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1/V_2 - 1)$. The drive current is then $I_{source} = V_1/R_{source}$.